

WHAT IS CLAIMED IS:

1. A manufacturing method of a transfective TFT-LCD panel, comprising the steps of:

forming a first conductive layer on a substrate;

5 defining the first conductive layer to form a gate;

forming a dielectric layer thereon;

forming a channel over the gate;

forming a photo-resist block;

forming a second conductive layer;

10 defining the second conductive to form a source and a drain over the gate, meanwhile, forming a photo-reflective layer on the photo-resist block;

forming a protection layer thereon;

defining the protection layer, forming a first opening on the drain allowing part of the drain to be exposed, and forming a second opening on  
15 the photo-reflective layer allowing part of the photo-reflective layer to be exposed; and

forming a transparent electrode electrically connected to the drain and

the photo-reflective layer via the first and the second opening.

2. A manufacturing method according to claim 1, wherein a capacitor electrode set under the photo-resist block is formed during the step of defining the first conductive layer.

5 3. A manufacturing method according to claim 1, wherein the first conductive layer is a first metal layer.

4. A manufacturing method according to claim 1, wherein the substrate is a glass substrate.

10 5. A manufacturing method according to claim 1, wherein the photo-resist block is composed of positive photo-resist.

6. A manufacturing method according to claim 1, wherein the second conductive layer is a second metal layer.

7. A manufacturing method according to claim 1, wherein the transparent electrode is composed of indium-tin oxide (ITO).

15 8. A manufacturing method of a transfective TFT-LCD panel equipped with a transmissive area and a reflective area, comprising the steps of:

forming a thin film transistor and a capacitor electrode on the substrate, wherein a photo-reflective layer within the reflective area and a source and a drain of the thin film transistor are formed simultaneously; and

forming a transparent electrode within the transmissive area.

9. A manufacturing method according to claim 8, wherein the photo-reflective layer is formed largely above the capacitor electrode.

10. A manufacturing method according to claim 8, wherein a photo-resist block is formed on the capacitor electrode prior to the formation of the photo-reflective layer.

11. A transflective TFT-LCD panel, wherein the liquid crystal display panel, equipped with a transmissive area and a reflective area, further comprises:

a substrate,

a thin film transistor having a source, a drain and a gate formed on the substrate ;

a dielectric layer utilized to cover the gate;

a photo-resist block formed on the dielectric layer;

a photo-reflective layer formed on the photo-resist block, wherein the photo-reflective layer is located within the reflective area; and

a transparent electrode through which the photo-reflective layer is electrically connected to the drain, wherein the transparent electrode is formed largely within the transmissive area.

12. A liquid crystal display panel according to claim 11, further has a capacitor electrode which is formed on the substrate and is covered by the dielectric layer while the photo-resist block and the photo-reflective layer are situated above the capacitor electrode.

5

\* \* \* \* \*